

Radiation damage studies of new p-n junction SiC detectors

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Silicon Carbide is one of the most promising materials for radiation detectors due to the high resistance to radiation damage. In this work we present the study of the radiation damage of a new large, p-n junctions silicon carbide device developed by SiCILLA collaboration. Several devices under test were irradiated in different experimental conditions with different beams in order to study its general performance as a function of fluence.

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